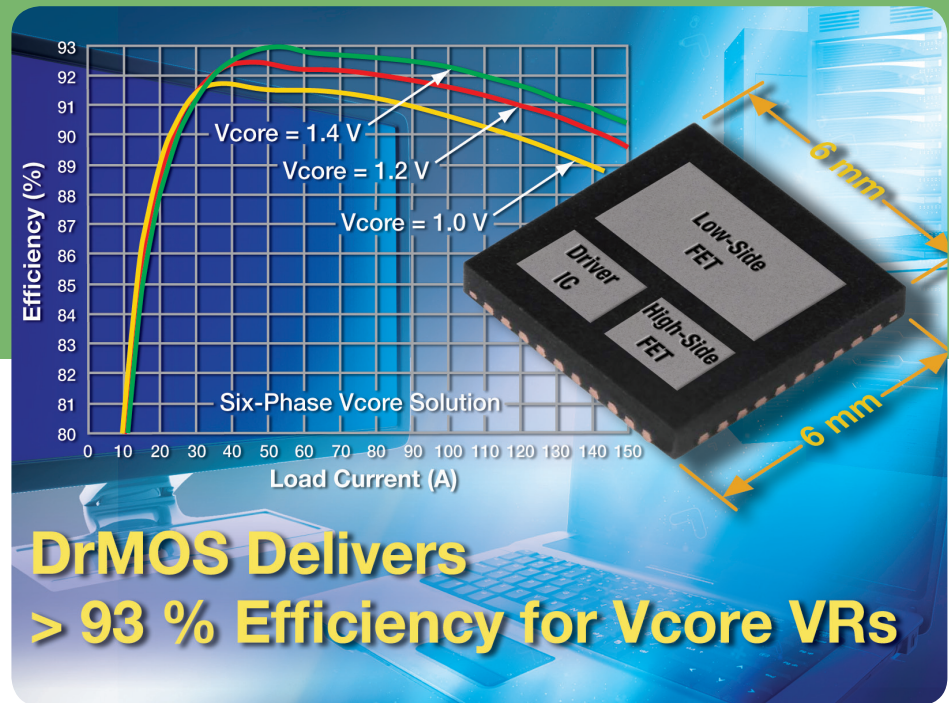




DrMOS SiC779CD



SiC779CD Integrated DrMOS Power Stage

The SiC779 is an integrated power stage that contains PWM optimized n-channel MOSFETs and a full featured MOSFET driver IC. The device complies with the Intel DrMOS standard. The SiC779 delivers up to 40 A continuous output current, and operates from an input voltage range of 3 V to 16 V. The integrated MOSFETs are optimized for output voltages in the range of 0.8 V to 2.0 V with a nominal input of 12 V. The device also delivers very high power at a 5 V output for ASIC applications.

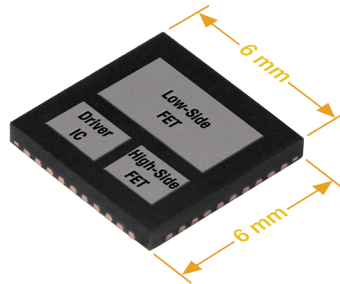
BENEFITS

- Higher efficiency
- Better thermal performance
- Integrated Schottky diode
- Allows designers to shrink PCB area
- Increases power density
- Reduces component count
- Reduces overall system cost

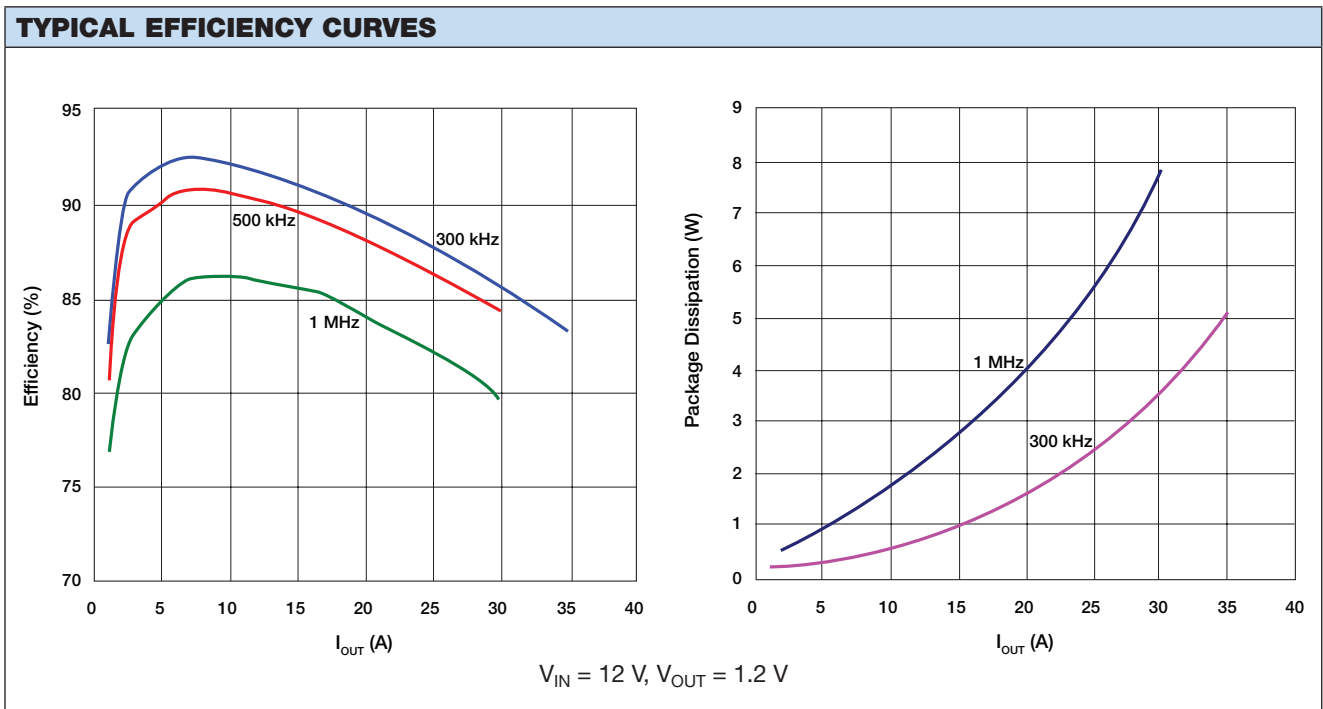
APPLICATIONS

- CPU and GPU core voltage regulation
- Servers, computers, workstations, game consoles, graphics boards, and PCs

SiC779CD Integrated DrMOS Power Stage



PARAMETRIC DATA							
Part number	V_{IN} Max	V_{CIN} bias supply (V)	V_{DRV} bias supply (V)	HS $R_{DS(on)}$ $V_{GH} = 5V$ (m Ω)	LS $R_{DS(on)}$ $V_{GH} = 5V$ (m Ω)	PWM Input	Package
SiC779CD	16	5.5	5.5	6	1.7	5 V	PowerPAK [®] MLP-40



SiC779CD TARGET APPLICATIONS

- Blade Servers
- Rack Servers
- Storage
- Notebooks
- Graphics Cards
- High End Desktops
- Game Consoles
- LCD TVs



Build **Vishay** into your **Design**

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For technical questions, contact PowerICtechsupport@vishay.com